

Silicon-organic hybrid electro-optic modulators for next generation optical interconnects

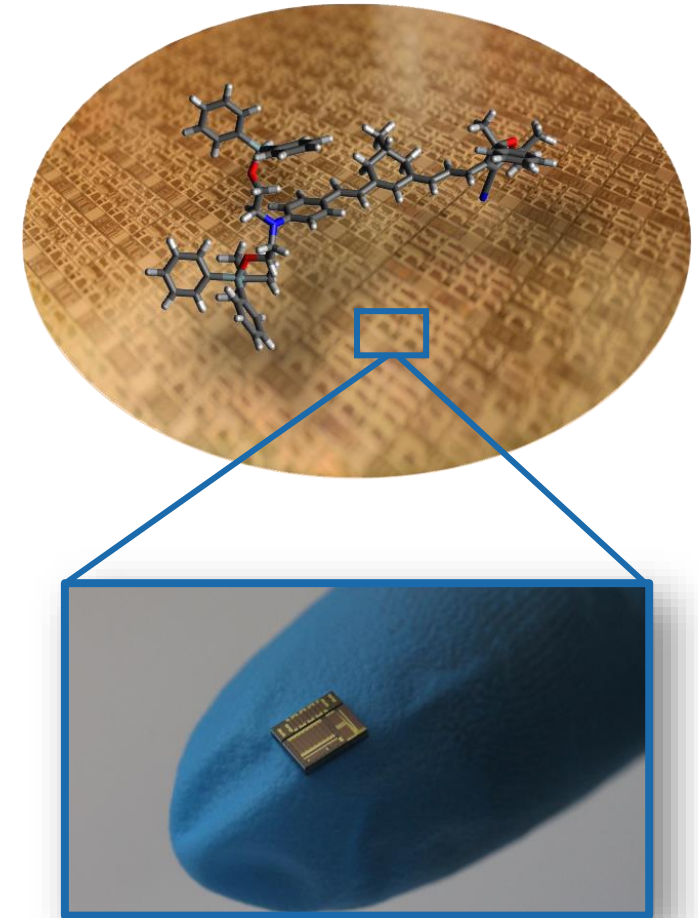
A. Mertens, SilOriX GmbH

Mission

SilOriX delivers components for **energy-efficient electro-optic conversion** of signals in **high-speed communication networks**. Our mission is to provide scalable and sustainable solutions by enhancing **silicon photonics** through **engineered organic materials**.

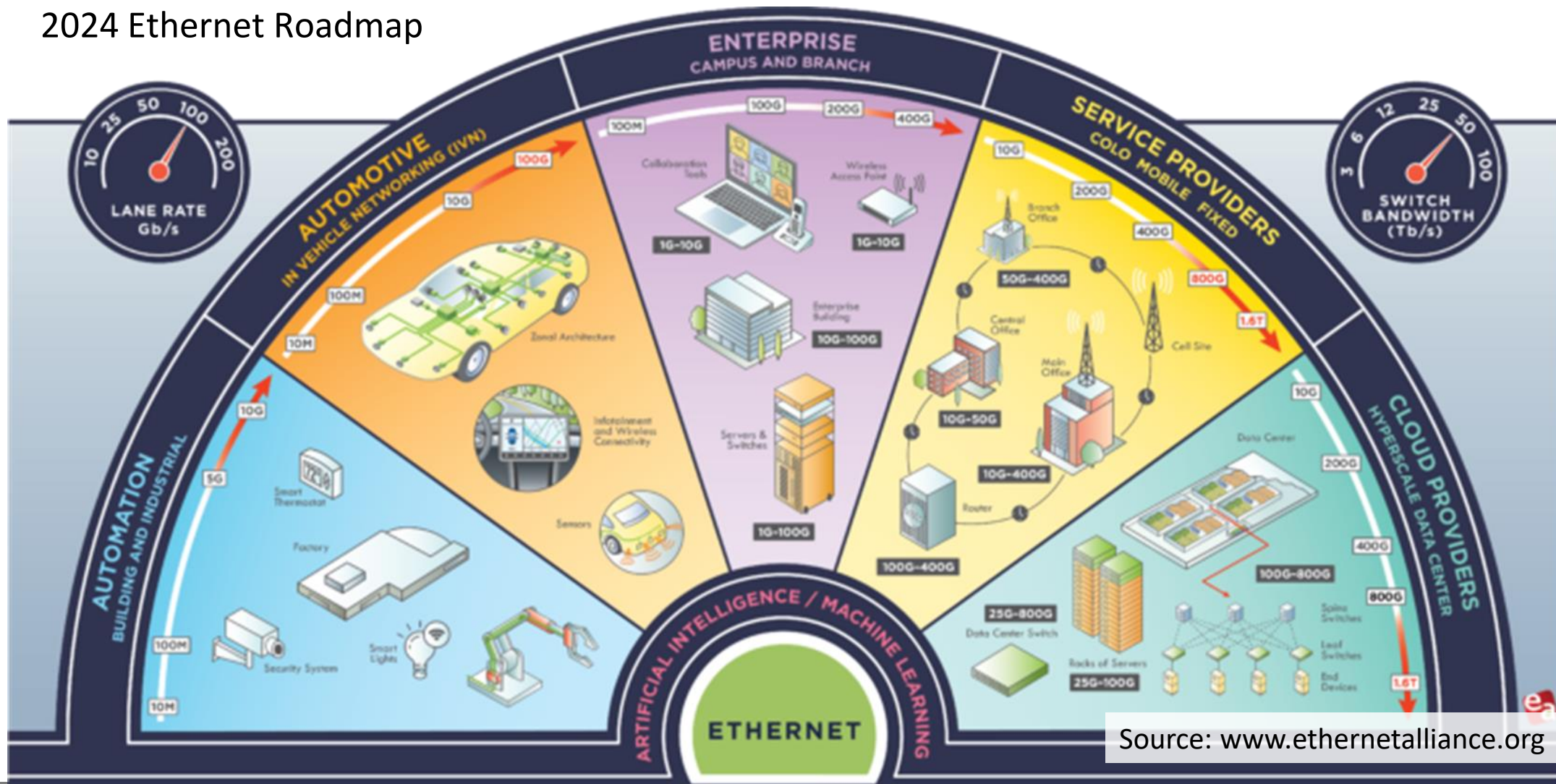
Vision

SilOriX will become **the technology leader and global supplier** of **silicon-organic hybrid (SOH)** photonic integrated circuits (PIC).



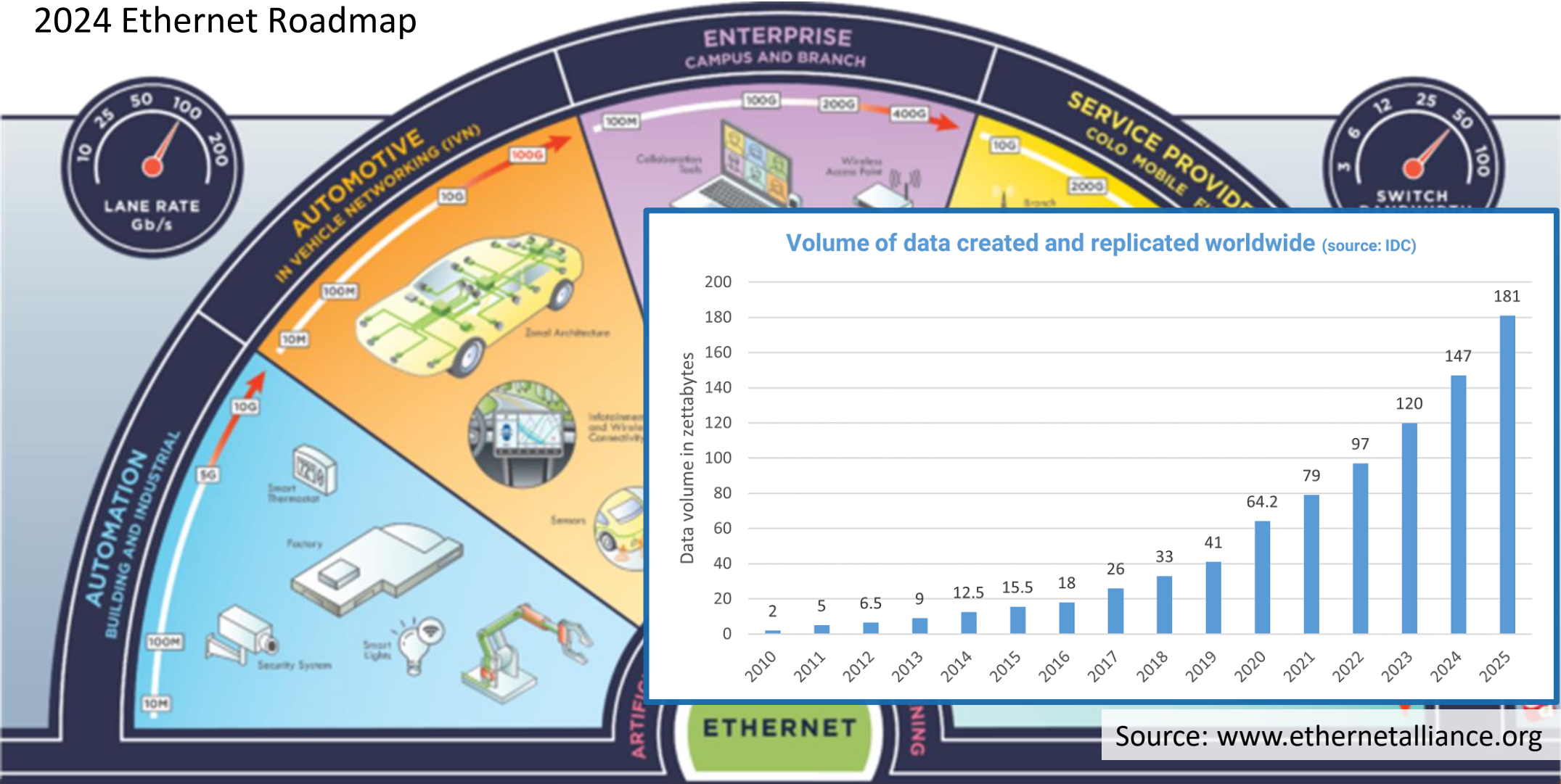
Application pull: Scalable optical communication networks

2024 Ethernet Roadmap



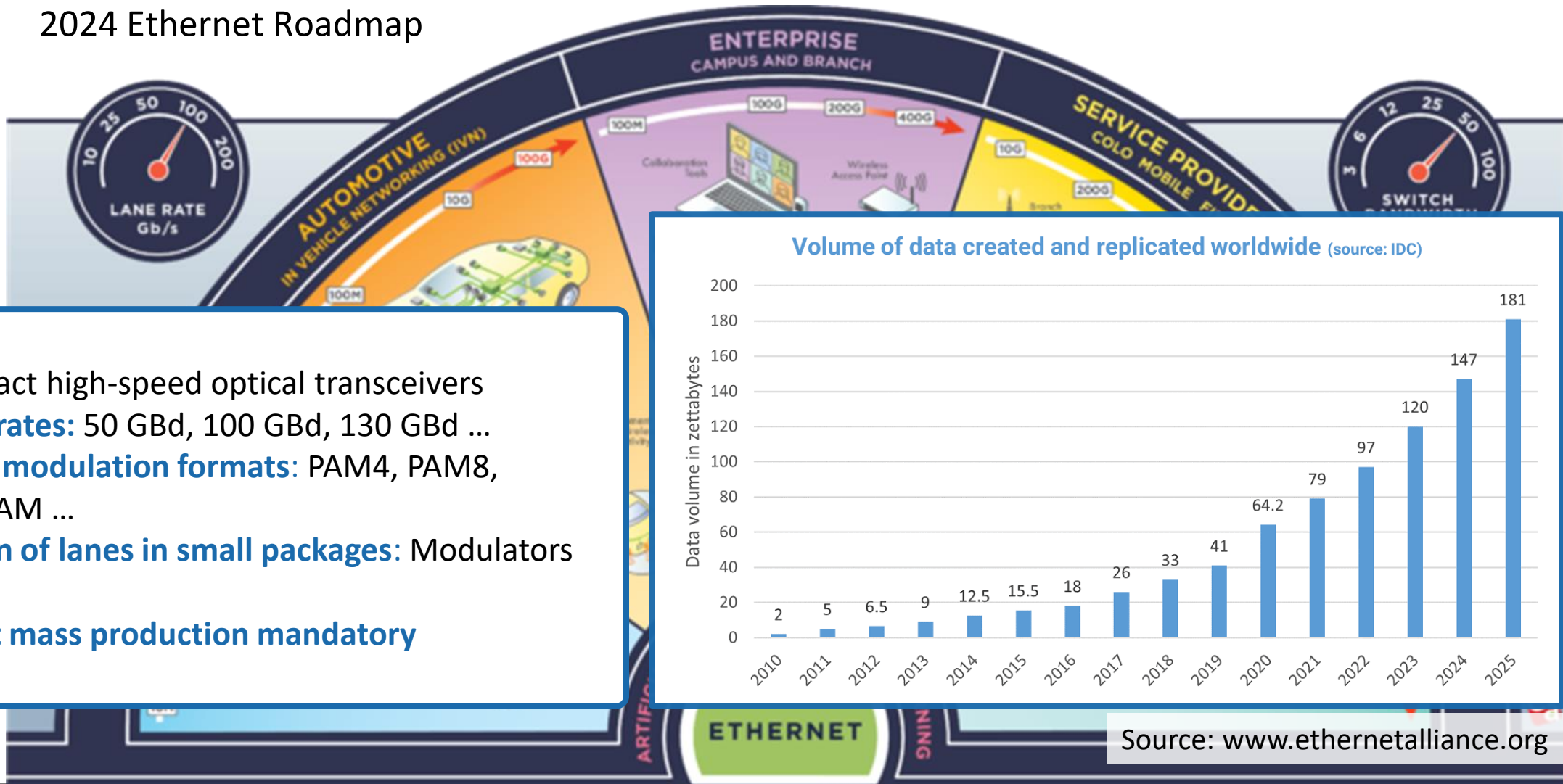
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2024 Ethernet Roadmap



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Technology push: Silicon photonics

Silicon photonics:

- High integration density
- Mature CMOS technology
 - Large-scale photonic-electronic integration with high yield
- Ecosystem of foundries
 - Fabless fabrication: Shared investment and development costs

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Silicon modulators

- Power hungry
- Bulky in size
- Limited in speed

Technology push: Silicon photonics

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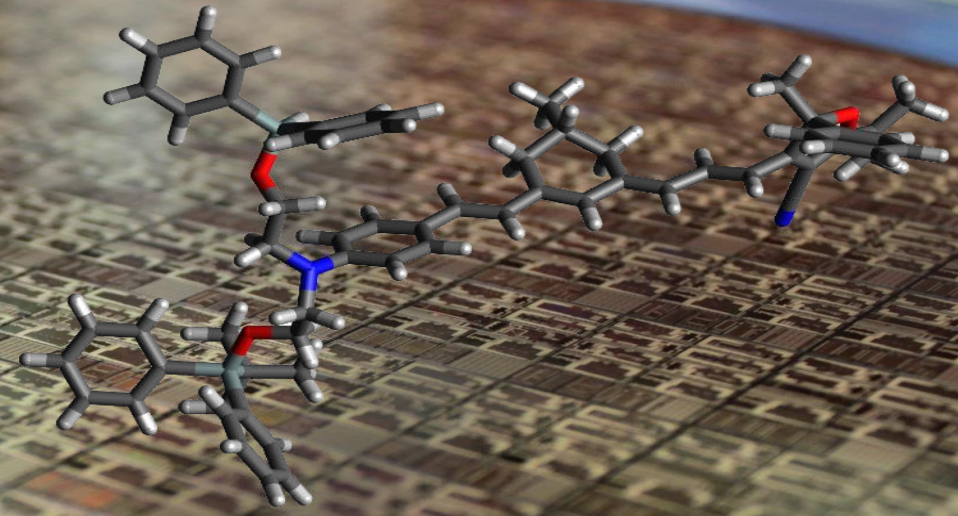
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Large-scale photonic-electronic integration with high yield
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Silicon modulators

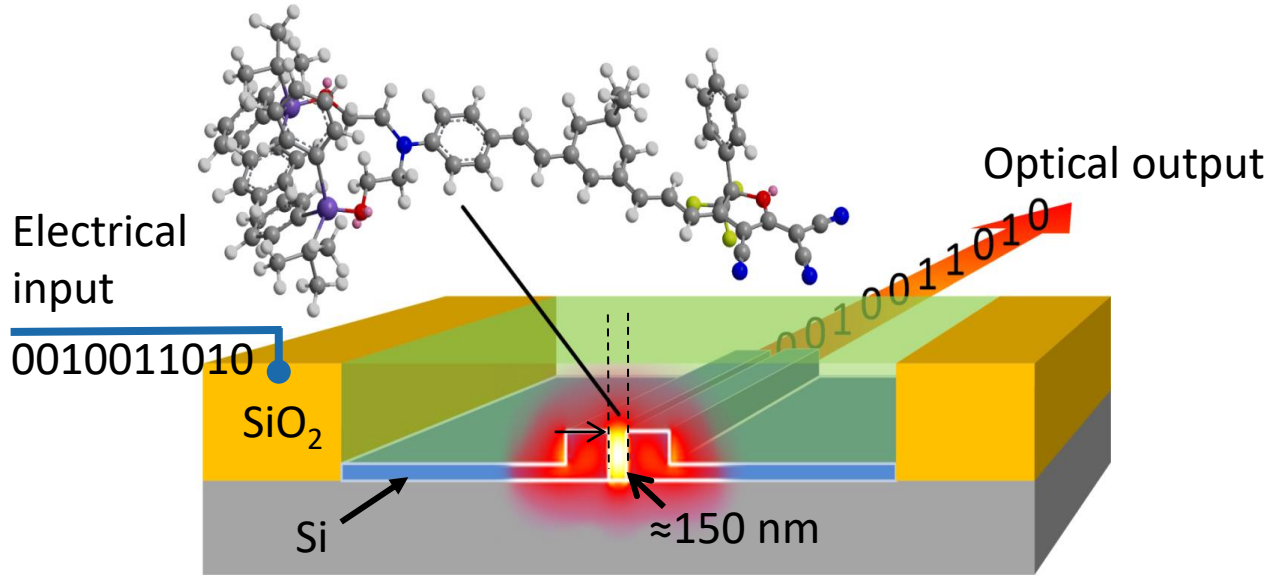
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Electro-optic molecules

- Material-efficient solution processes (e.g. inkjet printing)
- High-performance (r_{33} beyond 100 pm/V)
- Tailor-made materials for various applications



SOH Technology: Performance



Concept: Combine silicon-on-insulator waveguides with organic electro-optic cladding material

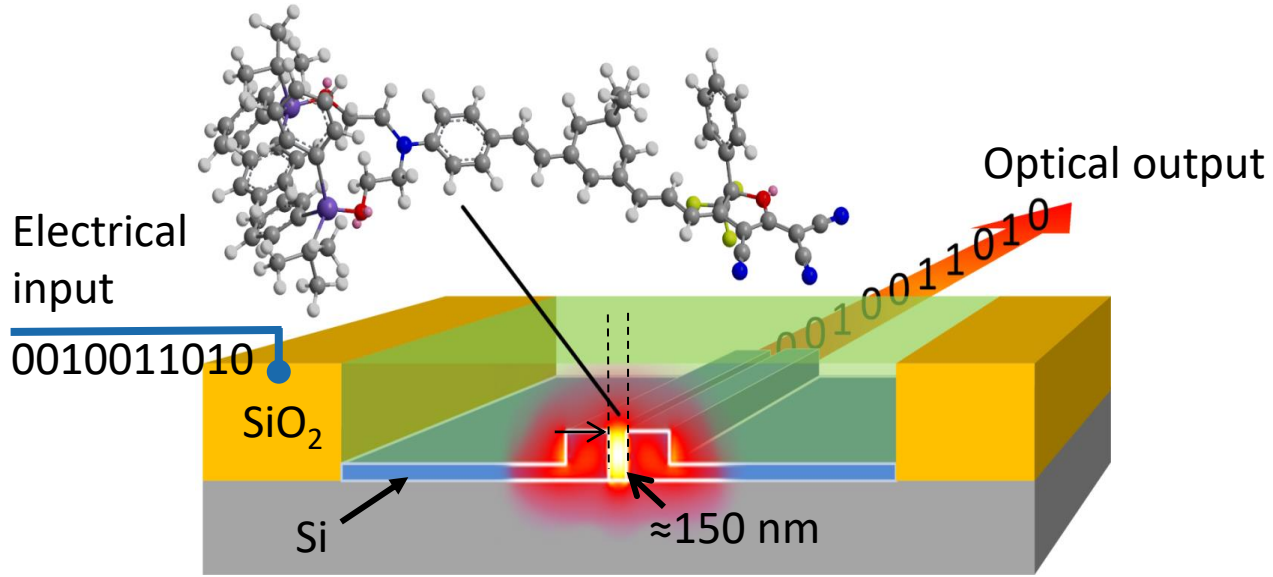
- **High-performance:** $r_{33} = 390 \text{ pm/V}$, $U_{\pi}L \approx 0.3 \text{ Vmm}$
- **Energy-efficient:** $< 1 \text{ V}_{pp}$, **few fJ/bit for Mach-Zehnder modulator**

Wolf *et al.*, Opt. Express **26**, 220-232 (2018)

Kieninger *et al.*, Optica **5**, 739 - 748 (2018)

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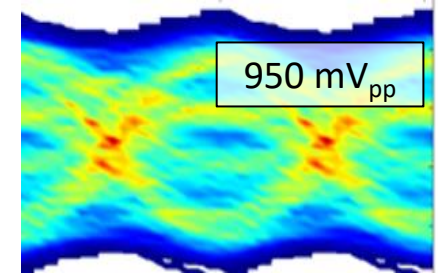
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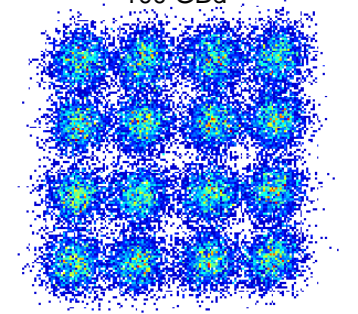
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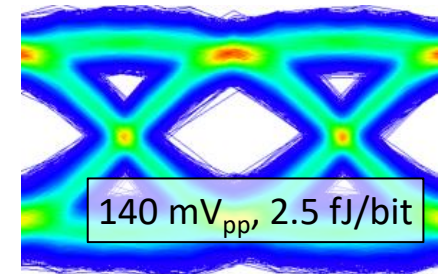
192 GBd PAM4
(384 Gbit/s)



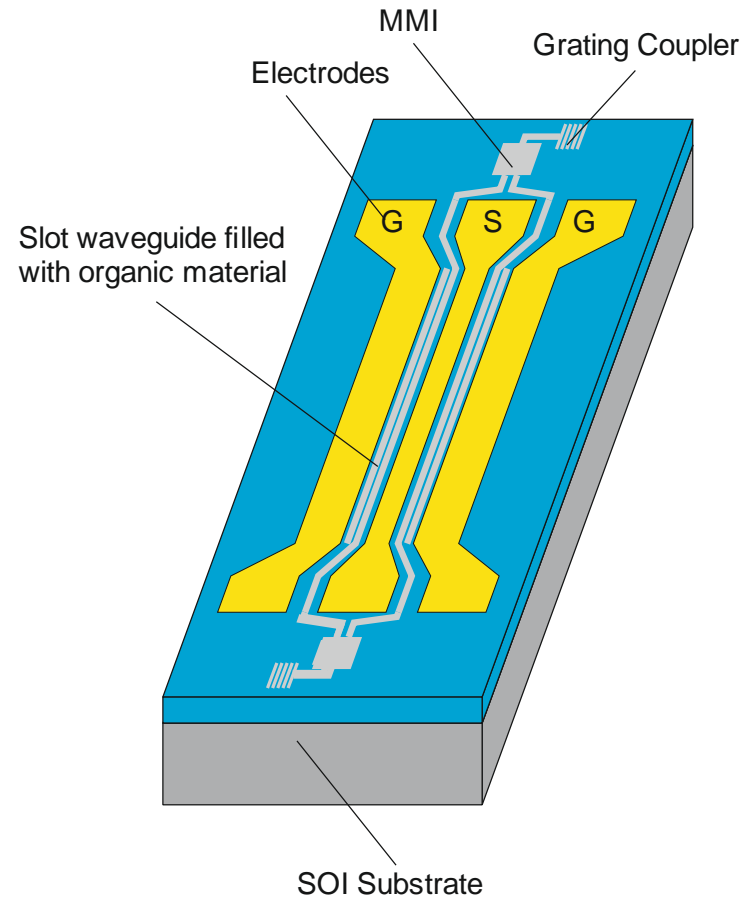
100 GBd 16 QAM
(400 Gbit/s per pol.)



40 Gbit/s OOK

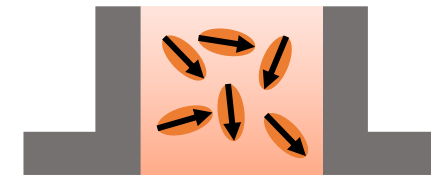
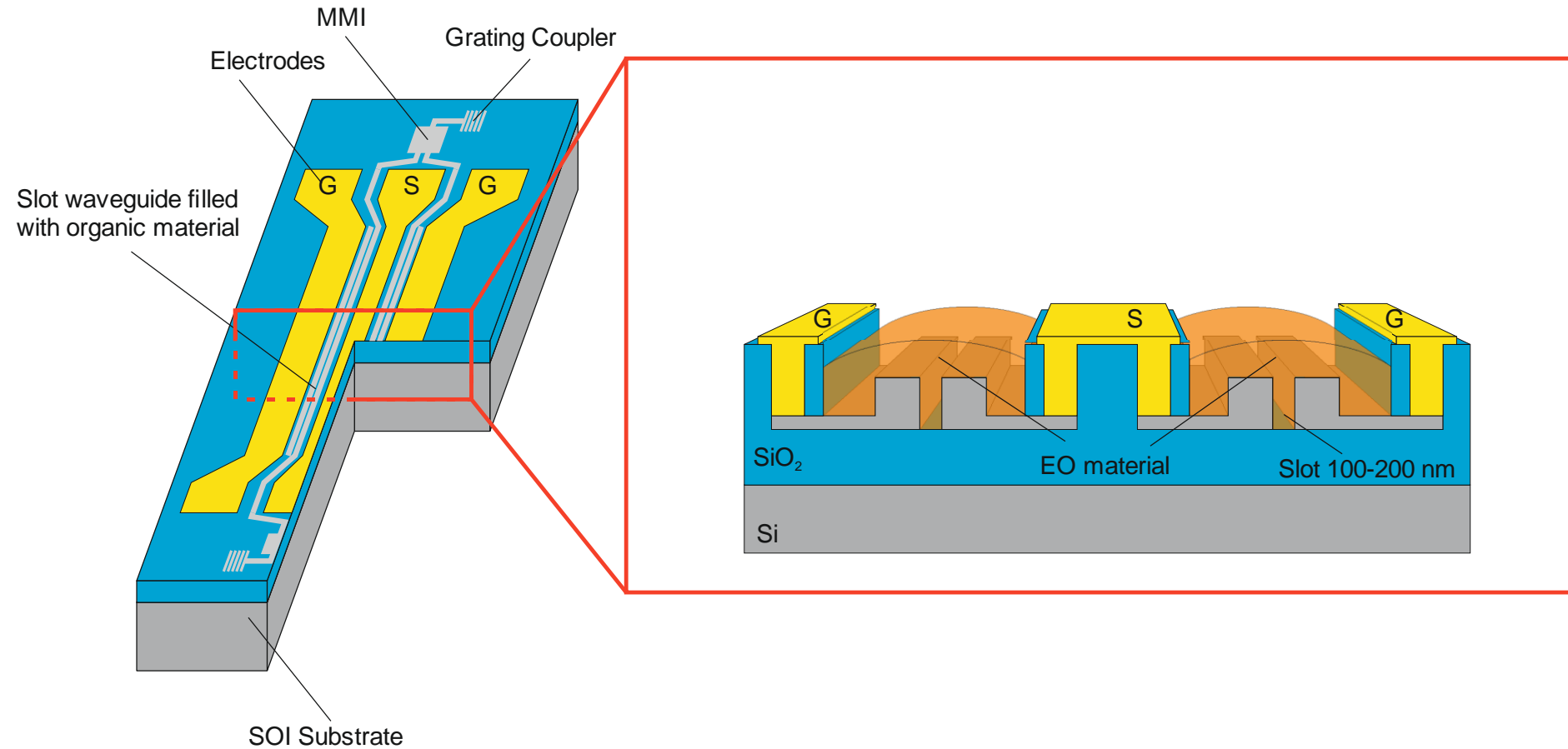


Core Technology: Silicon-Organic Hybrid (SOH) Integration

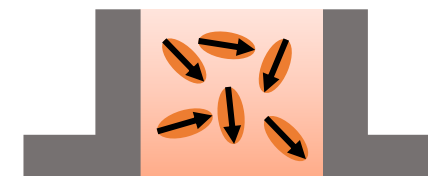
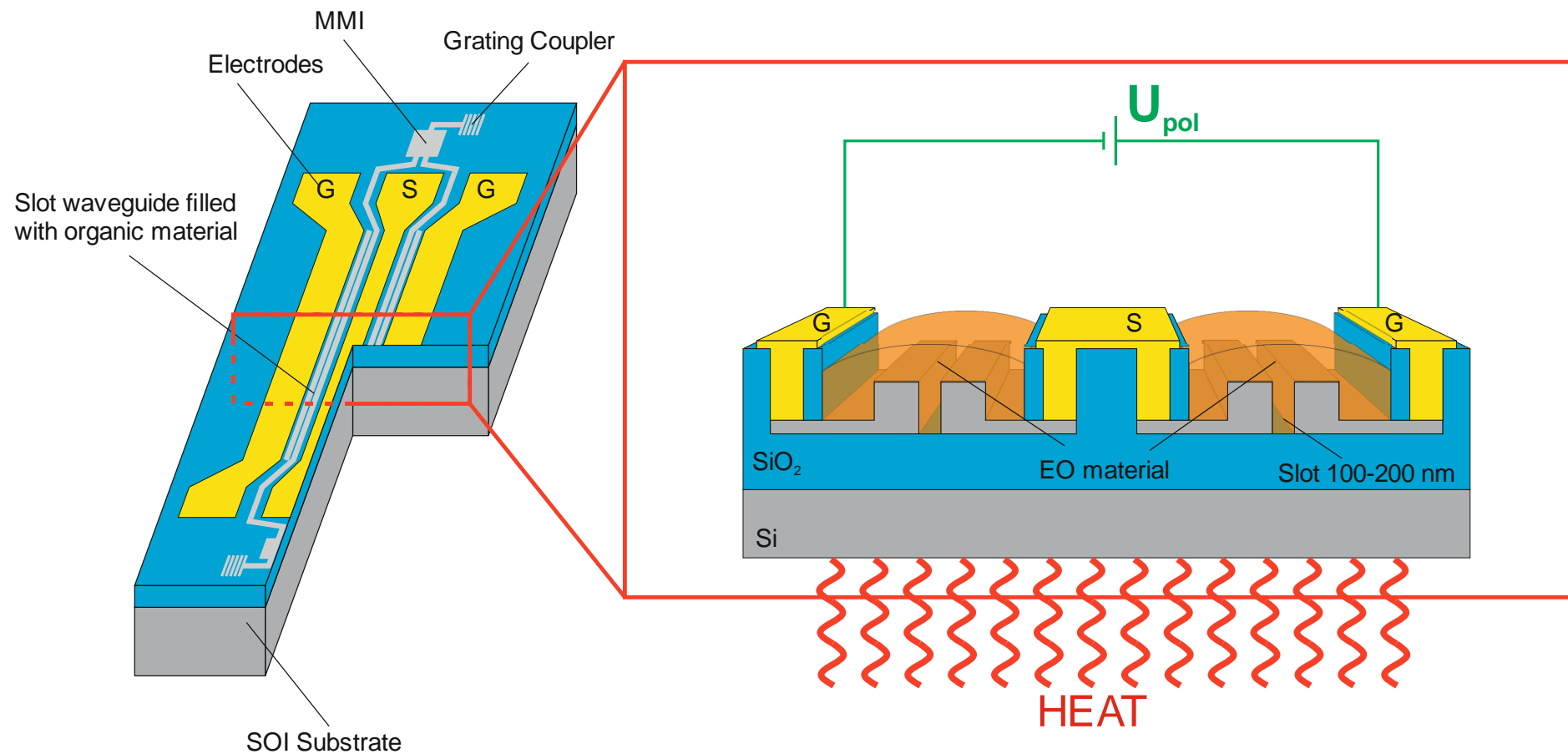


- Basic silicon photonic waveguide structures fabricated in **standard silicon photonic process** along with full portfolio of other devices (SiGe detectors *etc.*)
⇒ High integration density, high yield
- Organic EO materials deposited and poled in a **back-end post-processing step**
⇒ No compatibility conflicts with front-end CMOS processing

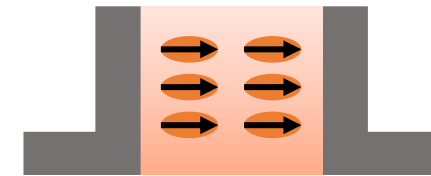
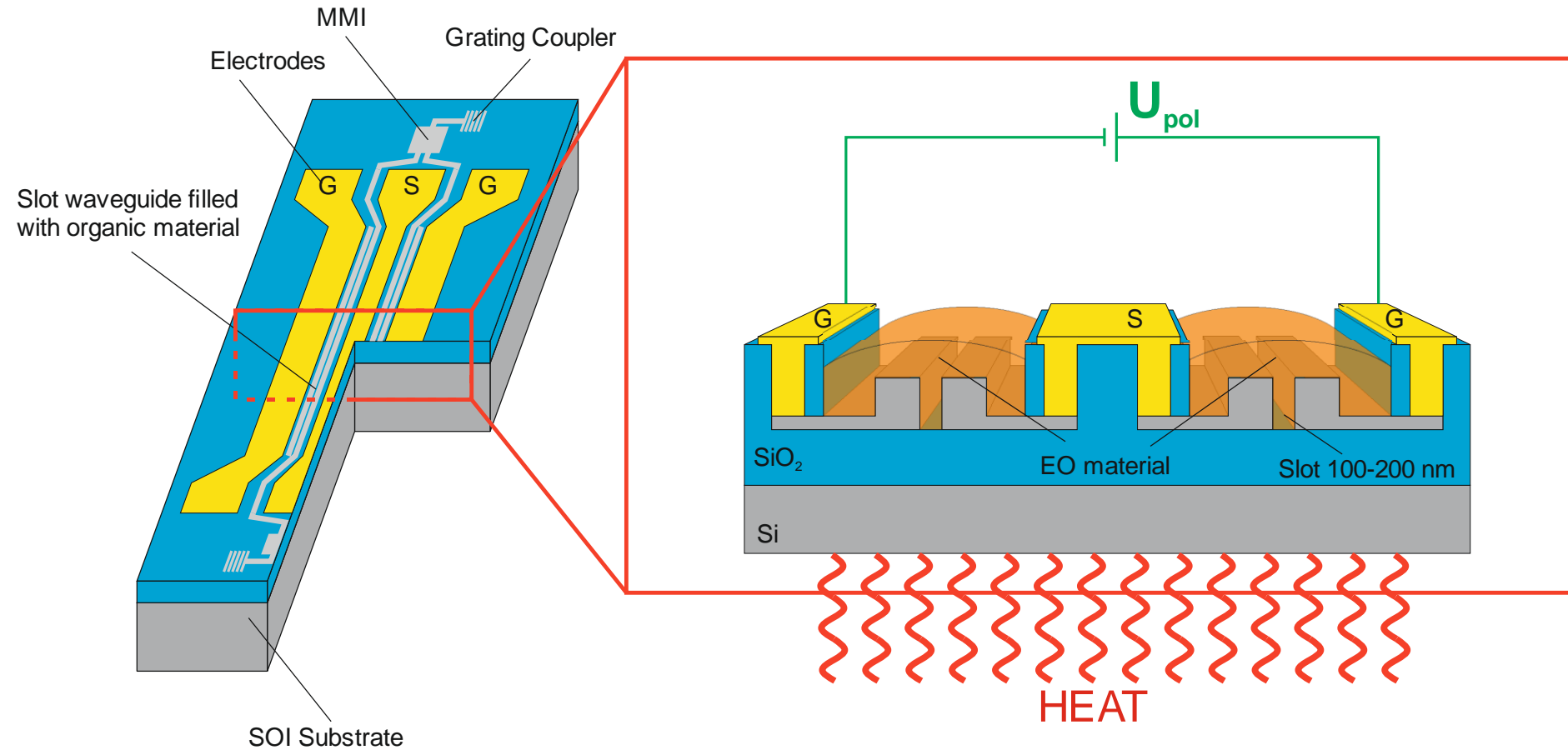
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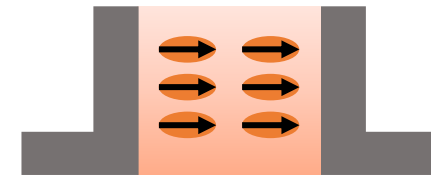
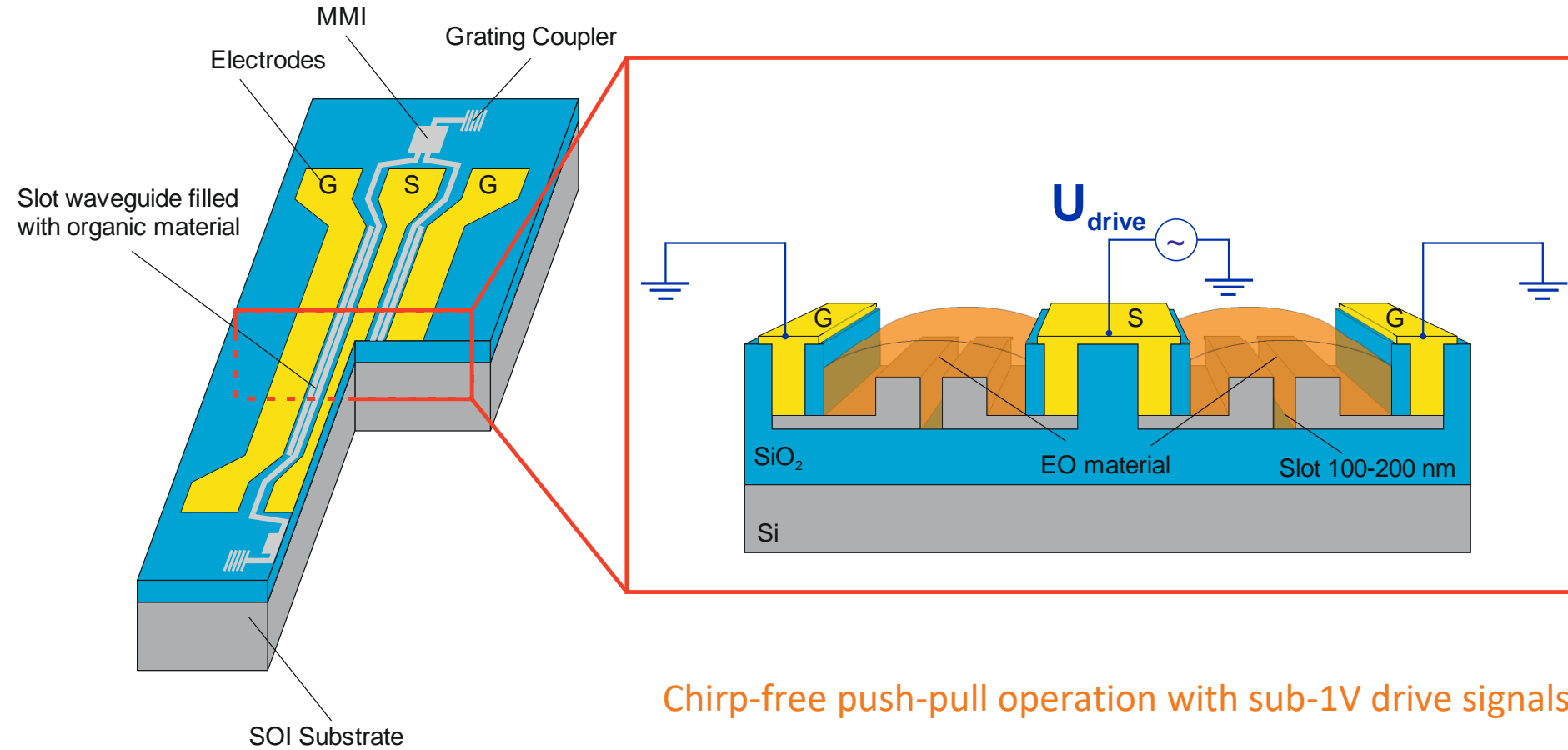
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Core Technology: Silicon-Organic Hybrid (SOH) Integration



Chirp-free push-pull operation with sub-1V drive signals.

Low drive-voltage hybrid silicon photonic modulator

Tentative specifications

General description

- Pockels-effect Mach-Zehnder modulator (MZM) or IQ modulator exploiting silicon-organic hybrid (SOH) technology
- Intensity modulation and direct detection (IMDD) @ ≥ 56 Gbd PAM4 (≥ 112 Gbit/s/λ)
- Coherent transmission @ ≥ 64 Gbd 64 QAM (≥ 960 Gbit/s/λ using polarization multiplexing)
- Low drive voltage (≤ 1 V_{pp}) and small foot print (≤ 1 mm)
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- Cost-efficient scalability to large-scale production

Applications

- Transceivers for datacom and telecom
 - Power-efficient $n \times 200$ Gbit/s ($n = 4, 8, 16, \dots$) IMDD links for data center and campus area networks
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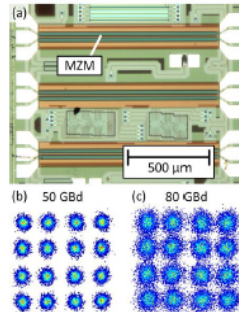


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RF impedance	50 Ω
Operating temperature ²	-270 °C – 85 °C
Maximum optical input power	15 dBm

Further information

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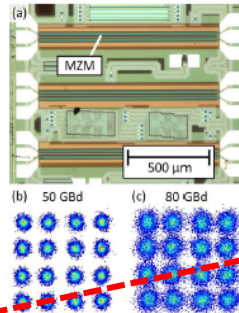


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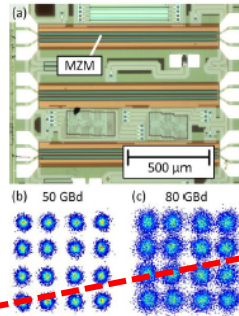


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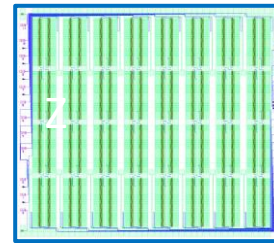
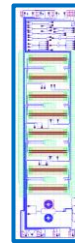
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8 x SOH 8 x pn-type SiP



1 mm

Standard configuration

DC π -voltage

Electro-optic bandwidth

On-chip optical loss

DC extinction ratio

Operating wavelengths

On-chip device footprint

π -voltage-length product

Chirp parameter

RF impedance

Operating temperature

Maximum optical input power

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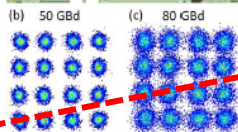
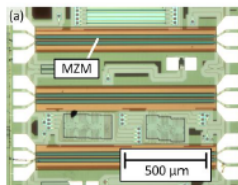


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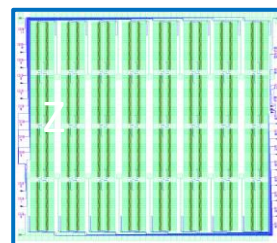
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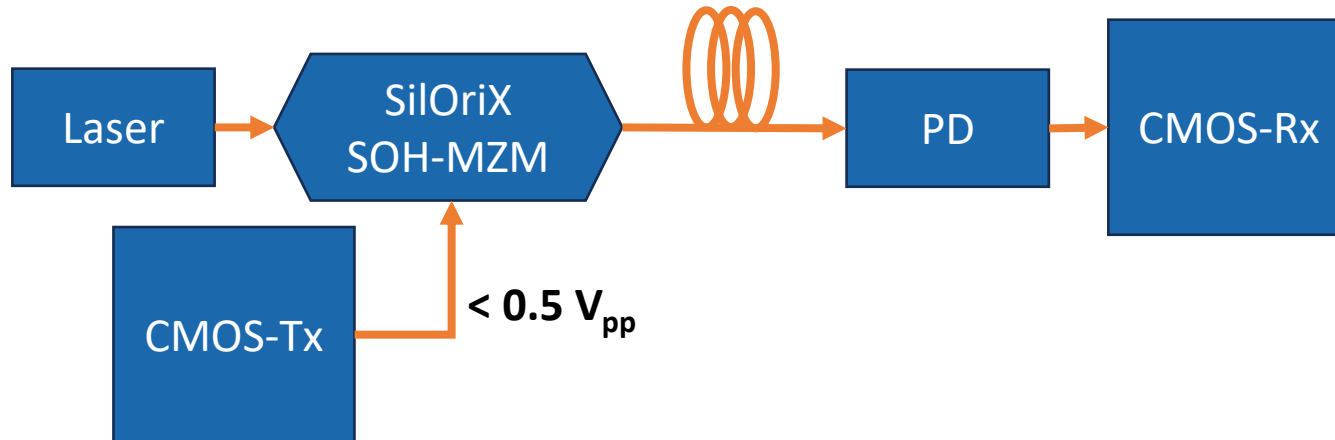
1 mm



- Monolithic co-integration with standard silicon photonics
- Operation by standard “CMOS-signals” without drive amplifier

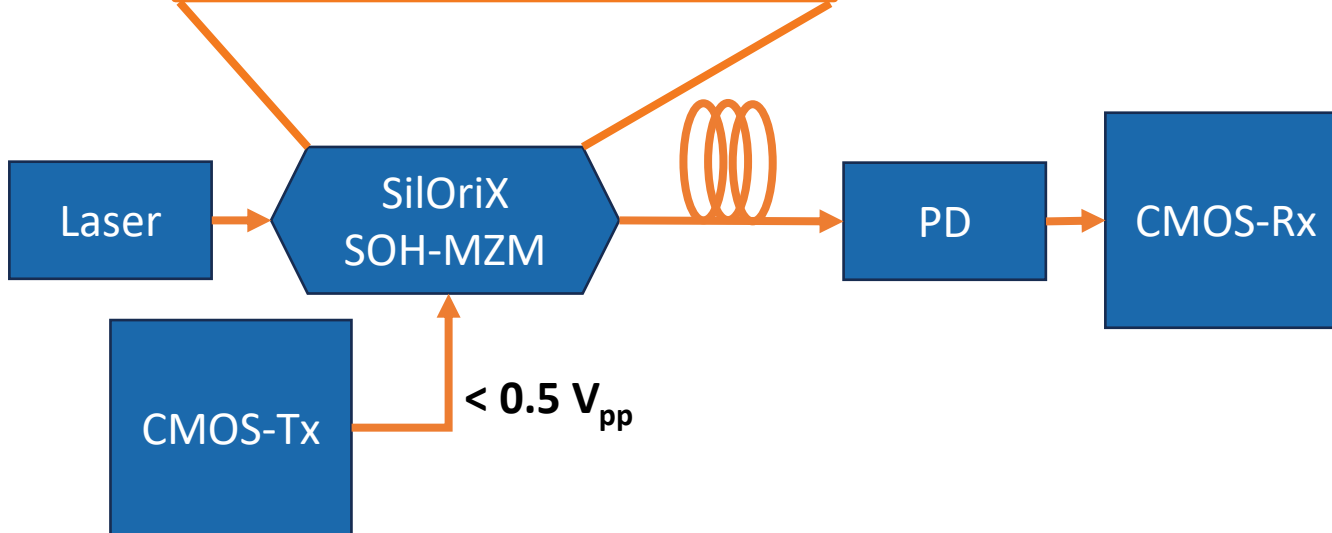
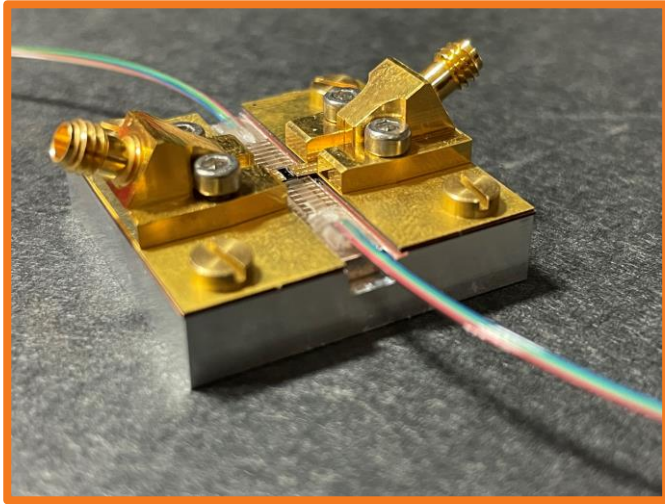
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Driver-less operation



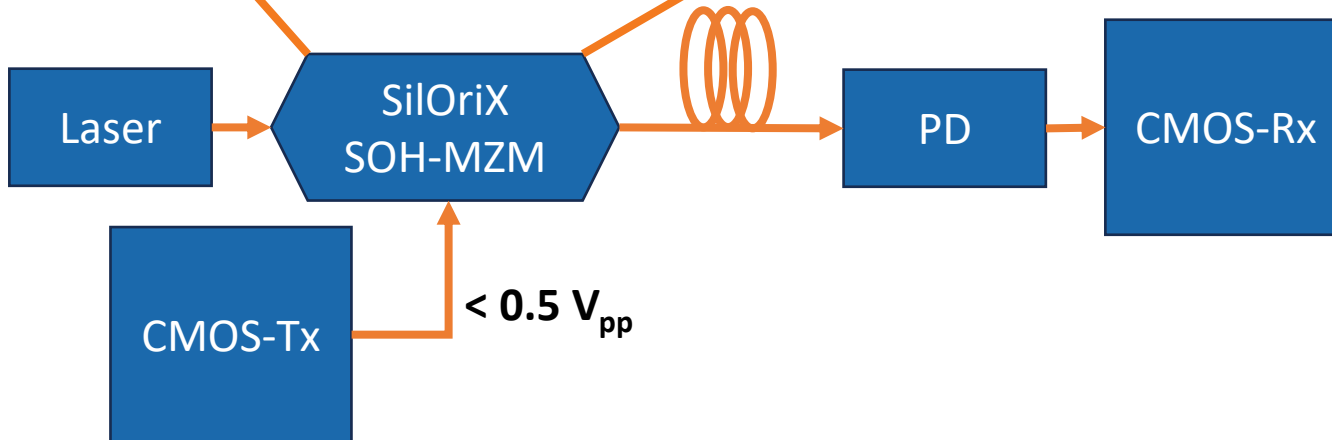
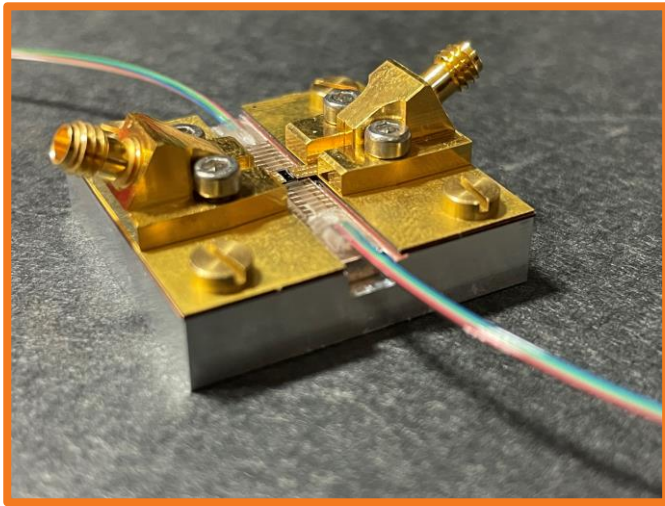
Schwarzenberger et al. OFC 2024 M3K.6

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Driver-less operation



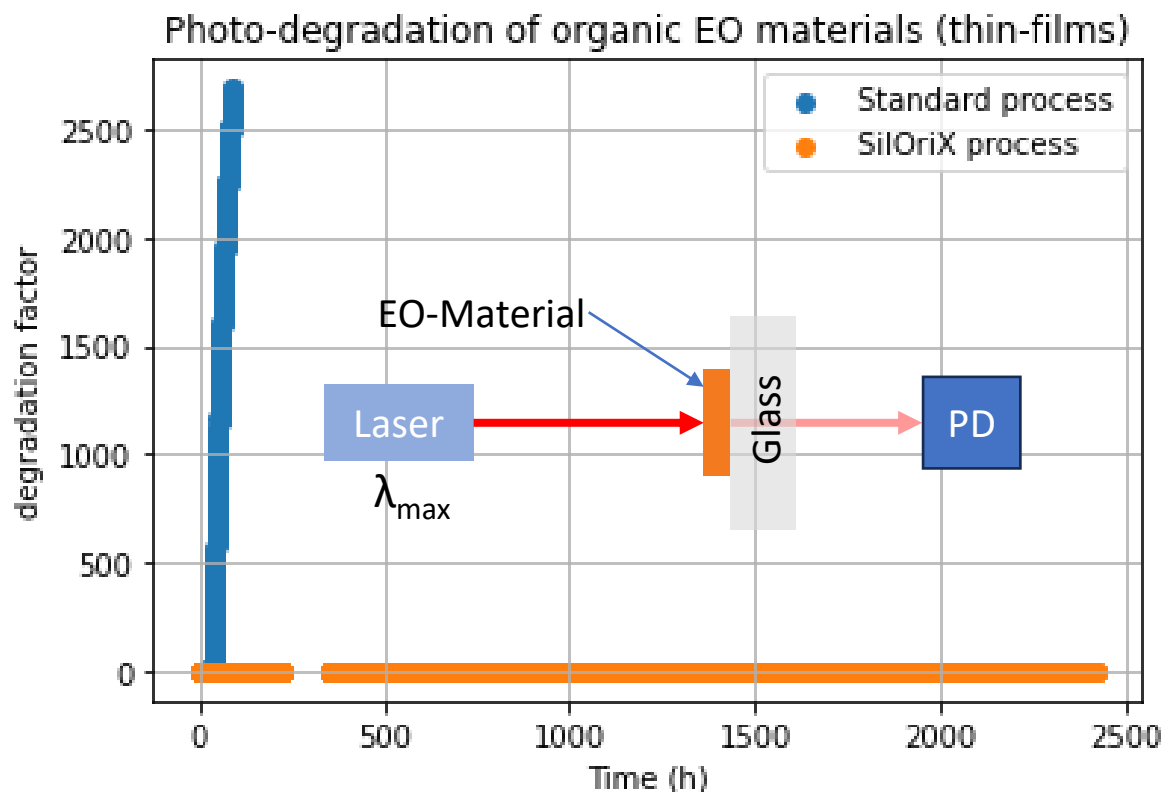
Schwarzenberger et al. OFC 2024 M3K.6

- Fully packaged SOH-modulator utilizing SilOriX's proprietary organic electro-optic materials and PIC designs.
- 112 Gbit/s PAM4 data transmission
- Driver-less operation at CMOS-compatible voltage swings below 0.5 V

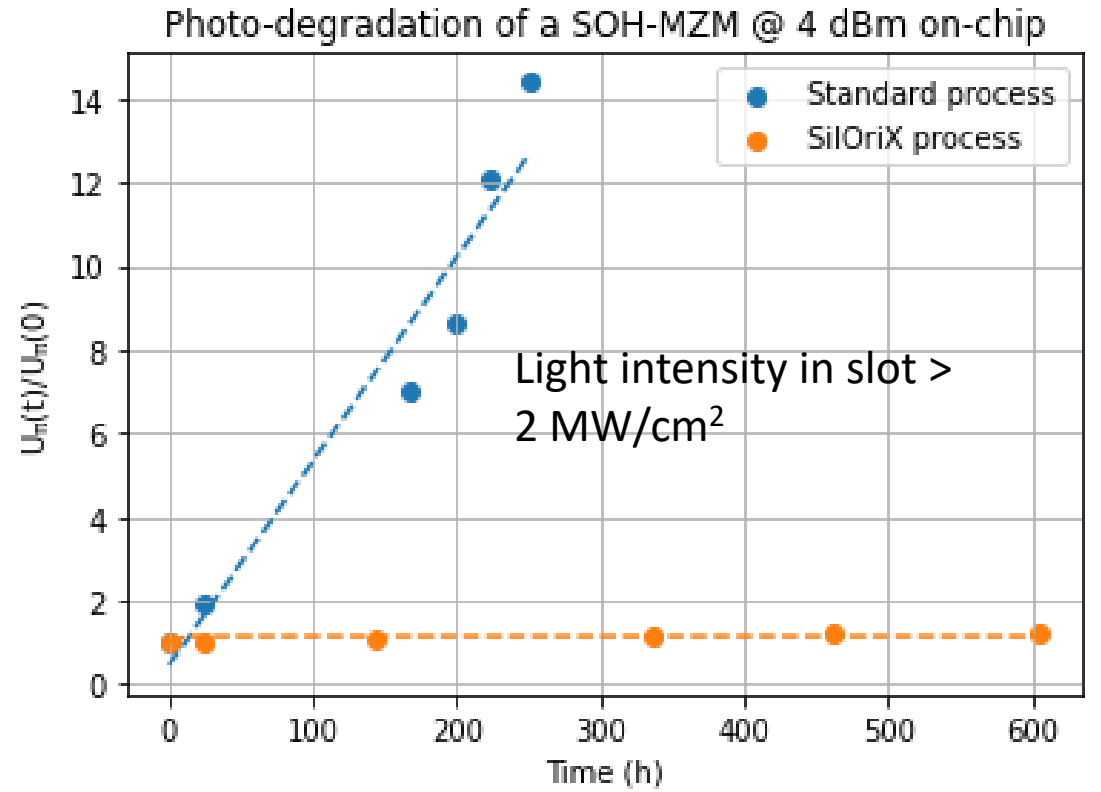
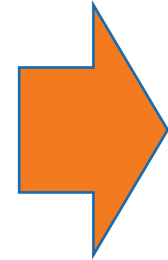
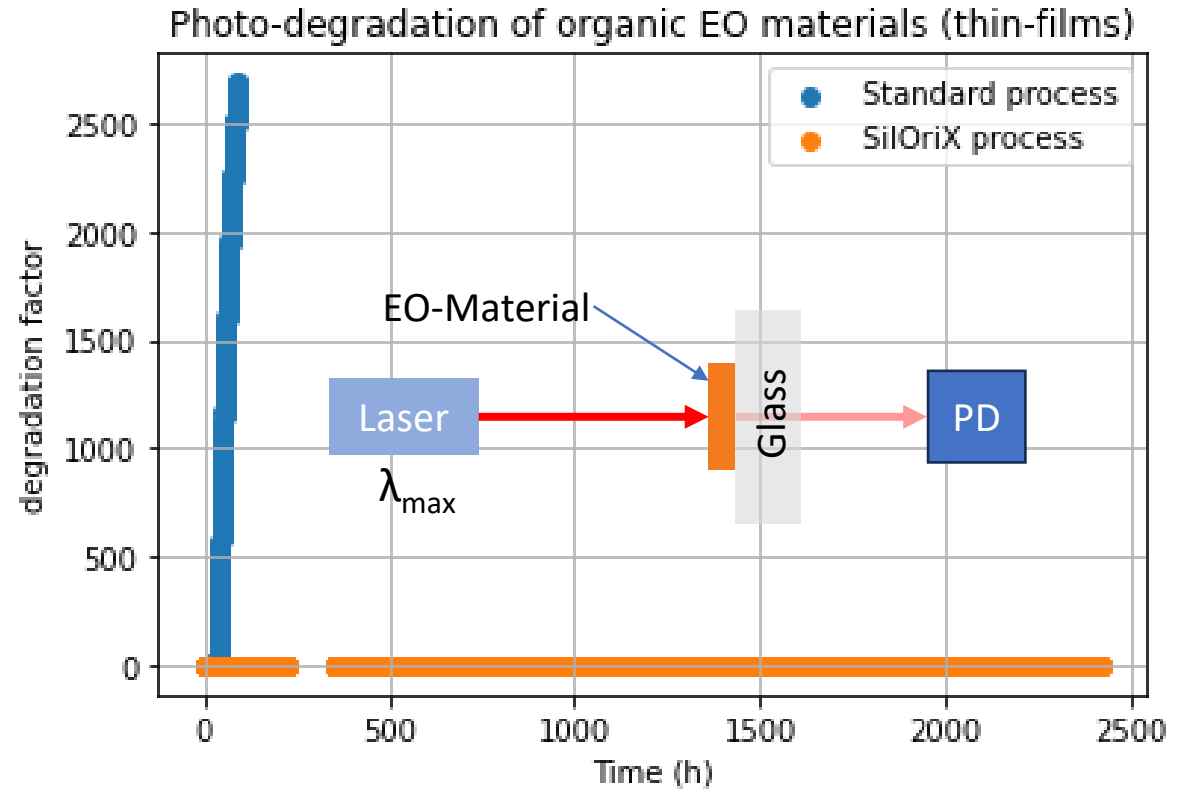
Long-term stable SOH modulators



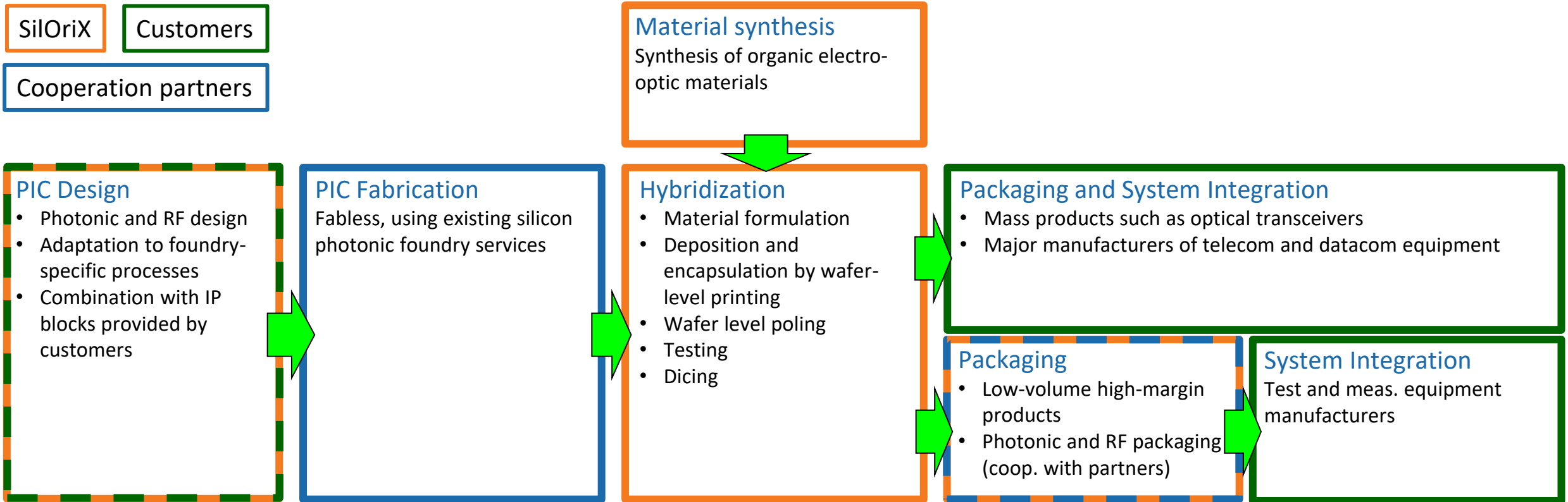
Long-term stable SOH modulators



Long-term stable SOH modulators



Value chain and product development



- Customized photonic integrated circuits (PIC) on a die level, for packaging and system integration by customers
- Customized packaged devices for high-margin niche applications
- PDK building blocks accessible through partner foundries
- Technology licensing for ultra-scale mass production by major transceiver manufacturers

Silicon-organic hybrid electro-optic modulators with disruptive performance

Efficient

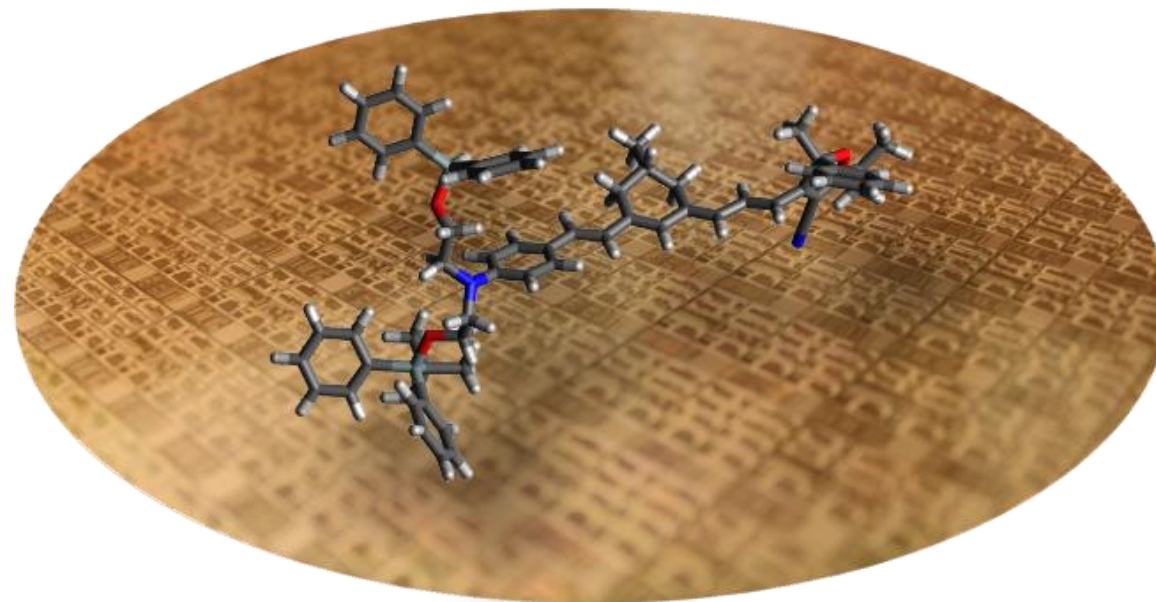
Sub-volt drive signals for ultra-low energy dissipation

Fast

Modulation at symbol rates of 190 GBd and beyond

Scalable

Monolithic back-end-of-line co-integration with established silicon photonics



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